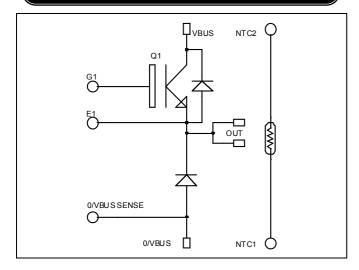


## Buck chopper Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1700V$$
  
 $I_{C} = 50A @ Tc = 80°C$ 

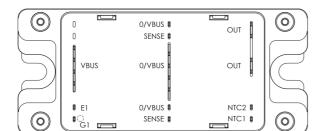


### **Application**

- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



#### **Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1700	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
$I_{C}$	Continuous Conector Current	$T_C = 80$ °C	50	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25$ °C	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	100A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		2.0	2.4	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 50A$	$T_j = 125$ °C		2.4		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1 \text{mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	=0V			400	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Condition	Test Conditions		Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			4400		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$			180		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		150			
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	ching (25°C)		370		
$T_{r}$	Rise Time	$V_{GE} = 15V$			40		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 50A$			650		
$T_{\mathrm{f}}$	Fall Time	$R_G = 10\Omega$		180			
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	ching (125°C)		400		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$ $V_{Bus} = 900V$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 50A$			800		115
$T_{\mathbf{f}}$	Fall Time	$R_G = 10\Omega$			300		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$	$T_j = 125$ °C		16		I ees
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_C = 50A$ $R_G = 10\Omega$	$T_j = 125$ °C		15	·	mJ

## **Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1700			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_{p}=1700V$	$T_j = 25^{\circ}C$			250	μA
1 <sub>RM</sub>	Waximum Reverse Leakage Current		$T_j = 125$ °C			500	μΛ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		50		A
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 50$ A	$T_i = 25^{\circ}C$		1.8	2.2	V
<b>V</b> F	Diode Forward Voluge	1 <sub>F</sub> - 30A	$T_{i} = 125^{\circ}C$		1.9		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		ns
·rr	Reverse Recovery Time	T 50 A	$T_{j} = 125^{\circ}C$		490		113
0	Reverse Recovery Charge	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu s$	$T_j = 25^{\circ}C$		14		"C
Q <sub>rr</sub>	di/dt =800A/ $\mu$ s $T_j = 125$		$T_{j} = 125^{\circ}C$		23		μC
Е	E <sub>r</sub> Reverse Recovery Energy	,	$T_j = 25$ °C		6		mJ
$\mathbf{E}_{\mathbf{r}}$		$T_{j} = 125^{\circ}C$		12		1113	



 $Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com for more information}).$ 

Symbol	Characteristic	Min	Тур	Max	Unit	
R <sub>25</sub>	Resistance @ 25°C		50		kΩ	
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K	

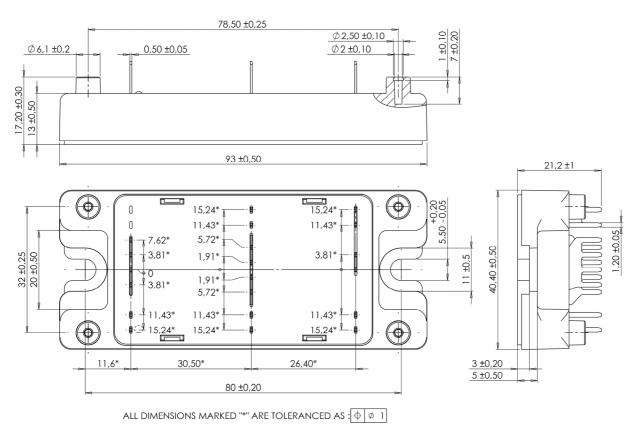
$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.4	°C/W
1\(\text{thJC}\)			Diode			0.7	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =	1 min, 50/60Hz		4000			V
$T_{J}$	Operating junction temperature range Storage Temperature Range		-40		150		
$T_{STG}$			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

### SP4 Package outline (dimensions in mm)

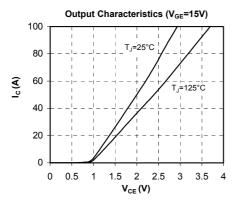


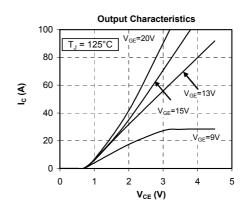
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

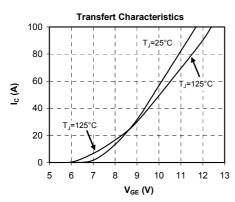
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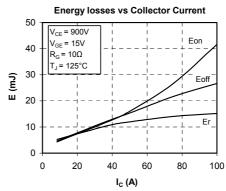


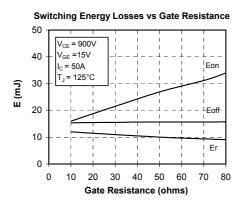
### **Typical Performance Curve**

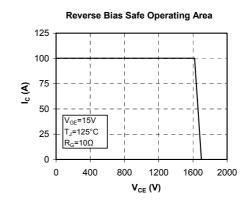


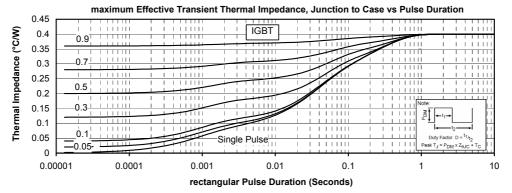




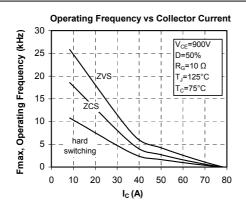


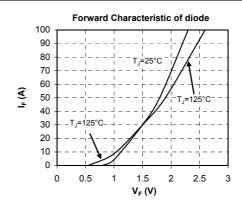


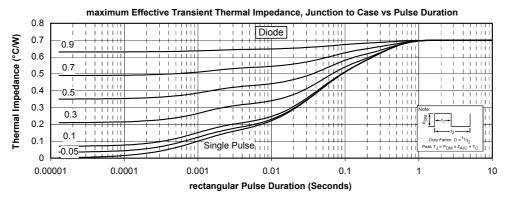














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